

### KSC2334

# **High Speed Switching Industrial Use** • Complement to KSA1010



### **NPN Epitaxial Silicon Transistor**

**Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

1.Base 2.Collector 3.Emitter

| Symbol           | Parameter                                    | Value      | Units |
|------------------|----------------------------------------------|------------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage                       | 150        | V     |
| V <sub>CEO</sub> | Collector-Emitter Voltage                    | 100        | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage                         | 7          | V     |
| I <sub>C</sub>   | Collector Current (DC)                       | 7          | А     |
| I <sub>CP</sub>  | *Collector Current (Pulse)                   | 15         | А     |
| I <sub>B</sub>   | Base Current (DC)                            | 3.5        | А     |
| P <sub>C</sub>   | Collector Dissipation (T <sub>C</sub> =25°C) | 40         | W     |
|                  | Collector Dissipation (T <sub>A</sub> =25°C) | 1.5        | W     |
| T <sub>J</sub>   | Junction Temperature                         | 150        | °C    |
| T <sub>STG</sub> | Storage Temperature                          | - 55 ~ 150 | °C    |

<sup>\*</sup> PW≤300μs, Duty Cycle≤10%

### Electrical Characteristics TC=25°C unless otherwise noted

| Symbol                                                   | Parameter                              | Test Condition                                                                                            | Min.           | Max.    | Units    |
|----------------------------------------------------------|----------------------------------------|-----------------------------------------------------------------------------------------------------------|----------------|---------|----------|
| V <sub>CEO</sub> (sus)                                   | Collector-Emitter Sustaining Voltage   | I <sub>C</sub> = 5A, I <sub>B1</sub> = 0.5A, L = 1mH                                                      | 100            |         | V        |
| V <sub>CEX</sub> (sus)1                                  | Collector-Emitter Sustaining Voltage   | $I_C = 5A$ , $I_{B1} = -I_{B2} = 0.5A$<br>$V_{BE}(off) = -5V$ , $L = 180\mu H$ , Clamped                  | 100            |         | V        |
| V <sub>CEX</sub> (sus)2                                  | Collector-Emitter Sustaining Voltage   | $I_C = 10A$ , $I_{B1} = 1A$ , $I_{B2} = -0.5A$ , $V_{BE}(off) = -5V$ , $L = 180\mu H$ , Clamped           | 100            |         | V        |
| I <sub>CBO</sub>                                         | Collector Cut-off Current              | $V_{CB} = 100, I_{E} = 0$                                                                                 |                | 10      | μΑ       |
| I <sub>CER</sub>                                         | Collector Cut-off Current              | $V_{CE} = 100V, R_{BE} = 51\Omega@T_{C} = 125^{\circ}C$                                                   |                | 1       | mA       |
| I <sub>CEX1</sub><br>I <sub>CEX2</sub>                   | Collector Cut-off Current              | $V_{CE} = 100V, V_{BE}(off) = -1.5V$<br>$V_{CE} = 100V, V_{BE}(off) = -1.5V$<br>@ $T_{CE} = 125^{\circ}C$ |                | 10<br>1 | μA<br>mA |
| I <sub>EBO</sub>                                         | Emitter Cut-off Current                | $V_{EB} = 5V, I_{C} = 0$                                                                                  |                | 10      | μΑ       |
| h <sub>FE1</sub><br>h <sub>FE2</sub><br>h <sub>FE3</sub> | * DC Current Gain                      | $V_{CE} = 5V, I_{C} = 0.5A$<br>$V_{CE} = 5V, I_{C} = 3A$<br>$V_{CE} = 5V, I_{C} = 5A$                     | 40<br>40<br>20 | 240     |          |
| V <sub>CE</sub> (sat)                                    | * Collector-Emitter Saturation Voltage | $I_C = 5A, I_B = 0.5A$                                                                                    |                | 0.6     | V        |
| V <sub>BE</sub> (sat)                                    | * Base-Emitter Saturation Voltage      | $I_C = 5A, I_B = 0.5A$                                                                                    |                | 1.5     | V        |
| t <sub>ON</sub>                                          | Turn On Time                           | $V_{CC} = 50V, I_{C} = 5A$                                                                                |                | 0.5     | μs       |
| t <sub>STG</sub>                                         | Storage Time                           | $I_{B1} = -I_{B2} = 0.5A$                                                                                 |                | 0.5     | μs       |
| t <sub>F</sub>                                           | Fall Time                              | $R_L = 10\Omega$                                                                                          |                | 1.5     | μs       |

<sup>\*</sup> Pulse Test: PW≤350μs, Duty Cycle≤2%Pulsed

### **h**<sub>FE</sub> Classification

| Classification   | R       | 0        | Y         |
|------------------|---------|----------|-----------|
| h <sub>FE2</sub> | 40 ~ 80 | 70 ~ 140 | 120 ~ 240 |

# **Typical Characteristics**

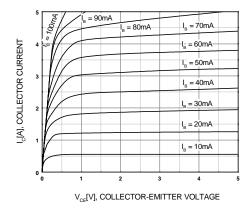


Figure 1. Static Characteristic

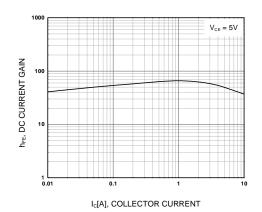


Figure 2. DC current Gain

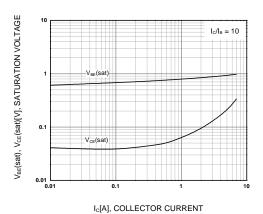


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

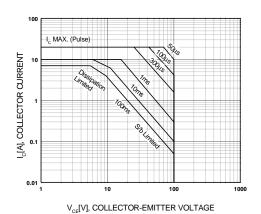


Figure 4. Safe Operating Area

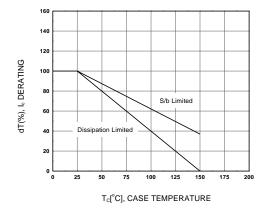


Figure 5. Derating Curve of Safe Operating Areas

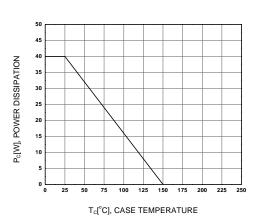
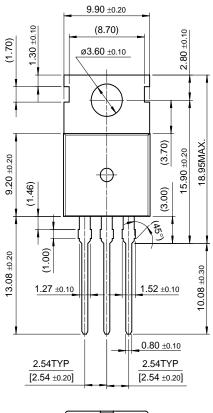


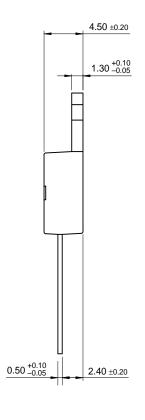
Figure 6. Power Derating

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# TO-220



**Package Demensions** 



10.00 ±0.20

Dimensions in Millimeters

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| CROSSVOLT™           | GlobalOptoisolator™ | Power247™                | SuperSOT™-6           |
| DenseTrench™         | GTO™                | PowerTrench <sup>®</sup> | SuperSOT™-8           |
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| EcoSPARK™            | ISOPLANAR™          | QS™                      | TruTranslation™       |
| E <sup>2</sup> CMOS™ | LittleFET™          | QT Optoelectronics™      | TinyLogic™            |
| EnSigna™             | MicroFET™           | Quiet Series™            | UHC™                  |
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